L Number	Hits	Search Text	DB	Time stamp
- Number	4	(("6069485") or ("5904490")).PN.	USPAT;	2003/12/04
			US-PGPUB; EPO; JPO;	11:22
		*	DERWENT;	
		485510104111	IBM_TDB	
-	2	("5610104").PN.	USPAT; US-PGPUB;	2003/12/03 18:40
			EPO; JPO;	10.40
	1		DERWENT;	
_	23044	transistor near2 structure	IBM_TDB USPAT;	2003/12/04
			US-PGPUB;	11:22
			EPO; JPO; DERWENT;	
			IBM_TDB	
-	11021	transistor adj structure	USPAT;	2003/12/04
			US-PGPUB; EPO; JPO;	11:23
			DERWENT;	
_	6868	/transistor add structure)	IBM_TDB	2002/12/24
_	0008	(transistor adj structure) and 257/\$.ccls.	USPAT; US-PGPUB;	2003/12/04
			EPO; JPO;	
	,		DERWENT; IBM TDB	
-	118	(base with gate with drain) with	USPAT;	2003/12/04
		insulator	US-PGPUB;	11:24
			EPO; JPO; DERWENT;	
			IBM_TDB	
-	13	((transistor adj structure) and 257/\$.ccls.) and ((base with gate with	USPAT;	2003/12/04
		drain) with insulator)	US-PGPUB; EPO; JPO;	11:36
			DERWENT;	
_	350	324/769.ccls.	IBM_TDB USPAT;	2003/12/04
	300	32.17703.0013.	US-PGPUB;	11:36
			EPO; JPO;	
			DERWENT; IBM TDB	
-	4	324/769.ccls. and (determin\$4 near5	USPAT;	2003/12/04
		capacitance) same (gate and source and drain)	US-PGPUB; EPO; JPO;	12:54
			DERWENT;	
_	4	/#5204025# #5402222# #5402222#	IBM_TDB	2003/12/04
-	4	("5304925" "5493231" "5493238" "5519336").PN.	USPAT	2003/12/04
- i	3	("5194923" "5268318" "5600578").PN.	USPAT	2003/12/04
_	371	(determin\$4 near5 capacitance) same (gate	USPAT;	12:54 2003/12/04
	7,1	and source and drain)	US-PGPUB;	13:05
			EPO; JPO;]
ļ			DERWENT; IBM TDB	
-	14	((determin\$4 near5 capacitance) same	USPĀT;	2003/12/04
		(gate and source and drain)) and measur\$4 near5 characteristic	US-PGPUB; EPO; JPO;	12:55
			DERWENT;	
_		//dotomined manuficulty	IBM_TDB	2002/10/2
-	4	((determin\$4 near5 capacitance) same (gate and source and drain)) and	USPAT; US-PGPUB;	2003/12/04 13:01
		324/766-769.ccls.	EPO; JPO;	
			DERWENT; IBM TDB	
-	356	((determin\$4 near5 capacitance) same	USPAT;	2003/12/04
		(gate and source and drain)) and	US-PGPUB;	13:06
	ļ	(transistor or integrated)	EPO; JPO; DERWENT;	
	ĺ		IBM TDB	

95	(((determin\$4 near5 capacitance) same	USPAT;	2003/12/04
	(gate and source and drain)) and (transistor or integrated)) and (bias adj voltage)	US-PGPUB; EPO; JPO; DERWENT;	13:37
12	(measur\$4 near5 capacitance near5 (transistor or (integrated adj circuit))) and 324/766-769.ccls.	USPAT; US-PGPUB; EPO; JPO;	2003/12/04 13:39
186	measur\$4 near5 capacitance near5 (transistor or (integrated adj circuit))	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/12/04 18:38
0	("406085019").PN.	IBM_TDB USPAT; US-PGPUB;	2003/12/04 16:13
9943	Aizawa.inv.	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/12/04 16:14
0	Aizawa.inv. and "406085019"	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/12/04 16:14
1	Aizawa.inv. and "06085019"	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/12/04 16:17
2	("6207477").PN.	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/12/04 16:17
186	measur\$4 near5 capacitance near5 (transistor or (integrated adj circuit))	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/12/04 18:38
781	measur\$4 near5 capacitance same (transistor or (integrated adj circuit))	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/12/05
52	(measur\$4 near5 capacitance same (transistor or (integrated adj circuit))) and (word or bit) adj line	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/12/04 18:39
2261	memory adj array adj2 cell	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/12/05 11:30
781	measur\$4 near5 capacitance same (transistor or (integrated adj circuit))	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/12/05 11:29
0	<pre>(memory adj array adj2 cell) and (measur\$4 near5 capacitance same (transistor or (integrated adj circuit)))</pre>	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/12/05 11:29
	186 0 9943 0 1 2 186 781 52 2261	voltage) (measur\$4 near5 capacitance near5 (transistor or (integrated adj circuit))) and 324/766-769.ccls. 186 measur\$4 near5 capacitance near5 (transistor or (integrated adj circuit)) 0 ("406085019").PN. 9943 Aizawa.inv. Aizawa.inv. and "406085019" 1 Aizawa.inv. and "06085019" 2 ("6207477").PN. 186 measur\$4 near5 capacitance near5 (transistor or (integrated adj circuit)) 781 measur\$4 near5 capacitance same (transistor or (integrated adj circuit)) 52 (measur\$4 near5 capacitance same (transistor or (integrated adj circuit)) and (word or bit) adj line 2261 memory adj array adj2 cell 781 measur\$4 near5 capacitance same (transistor or (integrated adj circuit)) 0 (memory adj array adj2 cell) and (measur\$4 near5 capacitance same (transistor or (integrated adj circuit))	DERWENT; IBM TDB USPĀT; US-PGPUB; EPO, JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO, JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DEWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT;

-	78	(memory adj array adj2 cell) and	USPAT;	2003/12/05
		(measur\$4 or determin\$4) with capacitance	US-PGPUB;	11:34
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	50		USPAT;	2003/12/05
		(measur\$4 or determin\$4) with	US-PGPUB;	13:37
		capacitance) and (word adj line) and (bit	EPO; JPO;	
		adj line)	DERWENT;	
			IBM TDB	
-	17		USPAT;	2003/12/05
		("4,498,044") or ("5,416,470") or	US-PGPUB;	13:38
		("5,701,101") or ("5,808,516") or	EPO; JPO;	
		("5,886,529") or ("5,986,456") or	DERWENT;	
		("6,054,867")).PN.	IBM TDB	